

ABSTRACT OF THE DISCLOSURE

The invention includes methods of forming particle-containing materials, and also includes semiconductor constructions comprising particle-containing materials. One aspect of the invention includes a method in which a first monolayer is formed across at least a portion of a semiconductor substrate, particles are adhered to the first monolayer, and a second monolayer is formed over the particles. Another aspect of the invention includes a construction containing a semiconductor substrate and a particle-impregnated conductive material over at least a portion of the semiconductor substrate. The particle-impregnated conductive material can include tungsten-containing particles within a layer which includes tantalum or tungsten.